TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SD1407A

Power Amplifier Applications

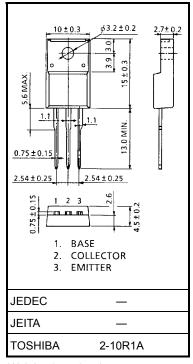
- High breakdown voltage: VCEO = 100 V
- Low collector saturation voltage: VCE (sat) = 2.0 V (max)
- Complementary to 2SB1016A

Maximum Ratings (Tc = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	100	V
Collector-emitter voltage	V _{CEO}	100	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	5	Α
Base current	lΒ	0.5	Α
Collector power dissipation (Tc = 25°C)	P _C	30	W
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55 to 150	°C

Industrial Applications

Unit: mm



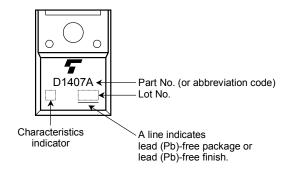
Weight: 1.7 g (typ.)

Electrical Characteristics (Tc = 25°C)

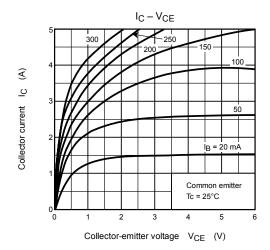
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 100 V, I _E = 0	_	_	100	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	1	mA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 50 mA, I _B = 0	100	_	_	V
DC current gain	h _{FE (1)} (Note)	V _{CE} = 5 V, I _C = 1 A	40	_	240	
	h _{FE (2)}	V _{CE} = 5 V, I _C = 4 A	20	_	_	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 4 A, I _B = 0.4 A	_	_	2.0	V
Base-emitter saturation voltage	V _{BE}	V _{CE} = 5 V, I _C = 1 A	_	_	1.5	V
Transition frequency	f _T	V _{CE} = 5 V, I _C = 1 A	_	12	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	100	_	pF

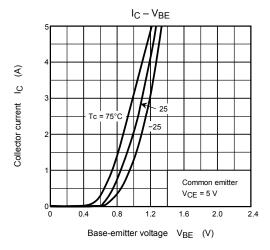
Note: hFE (1) classification R: 40 to 80, O: 70 to 140, Y: 120 to 240

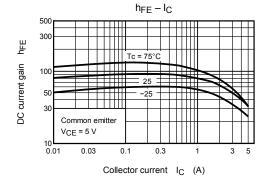
Marking

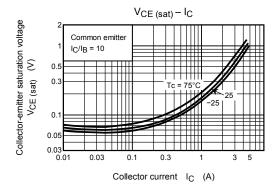


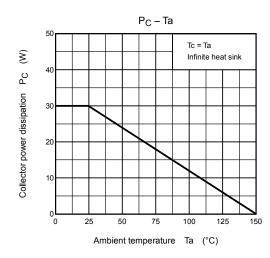
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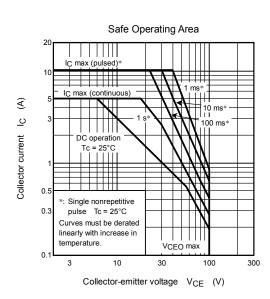












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Handbook" etc..

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